

10/602,915

AMENDMENT TO THE CLAIMS

1. (Currently amended) A semiconductor device comprising:
a gate insulating film having a multilayer structure including a zirconium oxide film and a high dielectric constant film which is formed of an oxide of a metal other than zirconium and substantially directly contacting the zirconium oxide film,
wherein the high dielectric constant film is a hafnium oxide film [[, a hafnium silicate film,]] or a hafnium aluminate film.
2. (Canceled)
3. (Original) The semiconductor device of claim 1, wherein the high dielectric constant film contains nitrogen.
4. (Original) The semiconductor device of claim 1, wherein the gate insulating film includes a zirconium silicate film formed under the zirconium oxide film.
- 5-20. (Canceled)
21. (New) A semiconductor device comprising:
a gate insulating film having a multilayer structure including a zirconium oxide film and a high dielectric constant film which is formed of an oxide of a metal other than zirconium and substantially directly contacting the zirconium oxide film,
wherein the high dielectric constant film is a hafnium oxide film, a hafnium silicate film, or a hafnium aluminate film,
wherein the gate insulating film includes a zirconium silicate film formed under the zirconium oxide film.